



MBR2045CT thru MBR2060CT

20.0A Schottky Barrier Rectifiers

Rectifier Reverse Voltage 100 to 200V

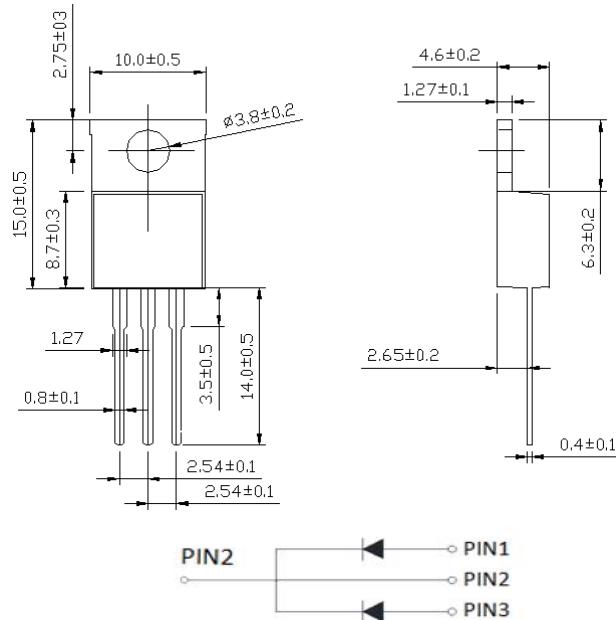
TO-220

Features

- High frequency operation
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- Guard ring for enhanced ruggedness and long term reliability
- Solder dip 260 °C max. 8 s, per JESD 22-B106

Mechanical Data

- **Package:** TO-220AB
Molding compound meets UL 94 V-0 flammability rating, RoHS-compliant
- **Terminals:** Tin plated leads, solderable per J-STD-002 and JESD22-B102
- **Polarity:** As marked



Dimensions in millimeters (1mm = 0.0394")

■Maximum Ratings ($T_a=25^\circ\text{C}$ Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	MBR2045CT	MBR2060CT
Device marking code			MBR2045CT	MBR2060CT
Repetitive Peak Reverse Voltage	V _{RRM}	V	45	60
Average Rectified Output Current @60Hz sine wave, R-load, $T_a=25^\circ\text{C}$	I _O	A	20	
Surge(Non-repetitive)Forward Current @60Hz half sine-wave, 1 cycle, $T_a=25^\circ\text{C}$	I _{FSM}	A	150	
Current Squared Time @1ms≤t<8.3ms $T_j=25^\circ\text{C}$,	I ² t	A ² s	94	
Storage Temperature	T _{stg}	°C		-55 ~ +175
Junction Temperature	T _j	°C		-55 ~ +150

■Electrical Characteristics ($T_a=25^\circ\text{C}$ Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	TEST CONDITIONS	MBR2045CT	MBR2060CT
Maximum instantaneous forward voltage drop per diode	V _{FM}	V	I _{FM} =10.0A	0.68	0.82
Maximum DC reverse current at rated DC blocking voltage per diode	I _{RRM1}	mA	V _{RM} =V _{RRM} $T_a=25^\circ\text{C}$	0.2	0.15
	I _{RRM2}		V _{RM} =V _{RRM} $T_a=125^\circ\text{C}$	20	
Thermal Resistance	Between junction and case		R _{θJ-C}	2.0	

Rating and Characteristic Curves ($T_A=25^\circ\text{C}$ Unless otherwise noted)

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